

SEP8736

AlGaAs Infrared Emitting Diode

FEATURES

- Side-looking plastic package
- 10° (nominal) beam angle
- 880 nm wavelength
- Enhanced coupling distance
- Mechanically and spectrally matched to SDP8436 phototransistor



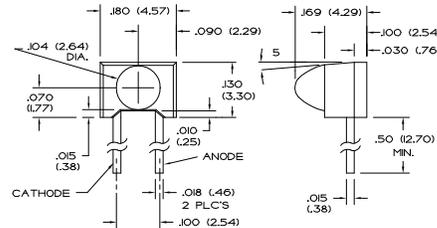
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DESCRIPTION

The SEP8736 is an aluminum gallium arsenide infrared emitting diode molded in a side-emitting smoke gray plastic package. The body and integral lens design combines the mounting advantage of a side-emitting package with the narrow emission pattern of a T-1 style device. The SEP8736 IRED is designed for those applications which require longer coupling distances than standard side-emitting devices can provide, such as touch screens. The IRED is also especially well suited to applications in which adjacent channel crosstalk could be a problem.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals ±0.005(0.12)
2 plc decimals ±0.020(0.51)



DIM_070.d54

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ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
|---------------------------------|---------------------------------|-----|-----|-----|--------------------|--------------------------|
| Irradiance ⁽¹⁾ | H | | | | mW/cm ² | I _F =20 mA |
| SEP8736-001 | | 0.5 | | | | |
| SEP8736-002 | | 1.2 | | 3.0 | | |
| SEP8736-003 | | 1.7 | | | | |
| Forward Voltage | V _F | | | 1.7 | V | I _F =20 mA |
| Reverse Breakdown Voltage | V _{BR} | 3.0 | | | V | I _R =10 μA |
| Peak Output Wavelength | λ _p | | 880 | | nm | |
| Spectral Bandwidth | Δλ | | 80 | | nm | |
| Spectral Shift With Temperature | Δλ _p /ΔT | | 0.2 | | nm/°C | |
| Beam Angle ⁽²⁾ | ∅ | | 10 | | degr. | I _F =Constant |
| Radiation Rise And Fall Time | t _r , t _f | | 0.7 | | μs | |

Notes

1. Measured in mW/cm² into a 0.104 (2.64) diameter aperture placed 0.500(12.7) from the lens tip.
2. Beam angle is defined as the total included angle between the half intensity points.

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

| | |
|-------------------------------|-----------------------|
| Continuous Forward Current | 50 mA |
| Power Dissipation | 100 mW ⁽¹⁾ |
| Operating Temperature Range | -40°C to 85°C |
| Storage Temperature Range | -40°C to 85°C |
| Soldering Temperature (5 sec) | 240°C |

Notes

1. Derate linearly from 25°C free-air temperature at the rate of 0.78 mW/°C.

SCHEMATIC

Anode



Cathode

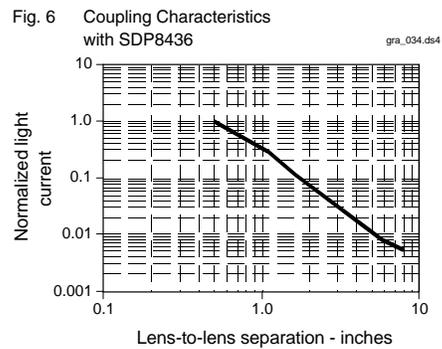
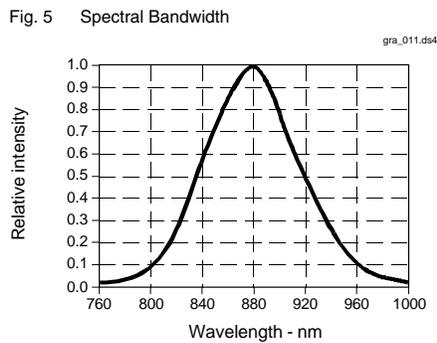
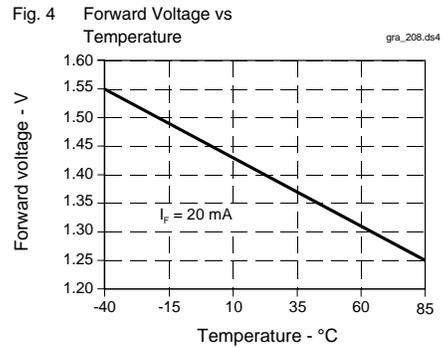
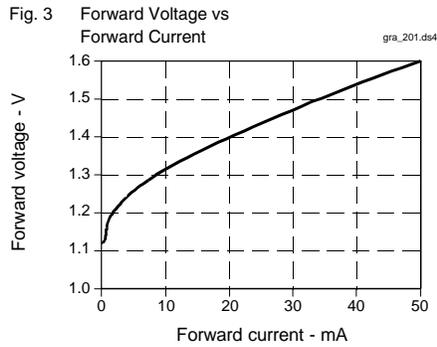
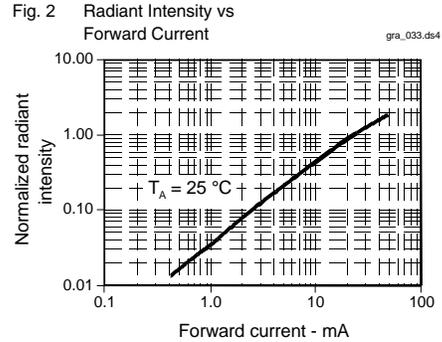
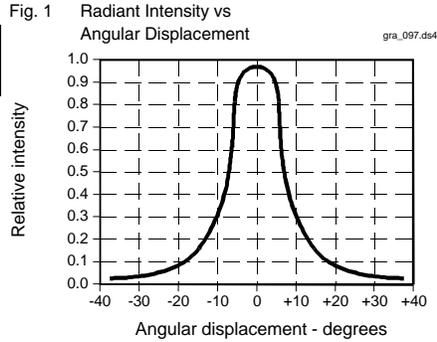
Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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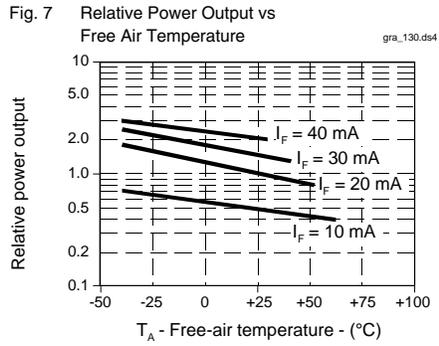
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All Performance Curves Show Typical Values

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